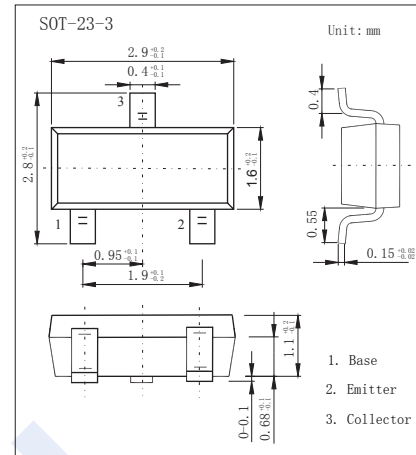


NPN Transistors

2SC1009

■ Features

- Collector Current Capability $I_C=50\text{mA}$
- Collector Emitter Voltage $V_{CE0}=30\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--------------------------------|-----------|------------|------------------|
| Collector - Base Voltage | V_{CBO} | 50 | V |
| Collector - Emitter Voltage | V_{CEO} | 30 | |
| Emitter - Base Voltage | V_{EBO} | 5 | |
| Collector Current - Continuous | I_C | 50 | mA |
| Collector Power Dissipation | P_C | 150 | mW |
| Junction Temperature | T_J | 125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -55 to 125 | |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|---|------|-----|------|---------------|
| Collector- base breakdown voltage | V_{CBO} | $I_C = 100 \mu\text{A}, I_E = 0$ | 50 | | | V |
| Collector- emitter breakdown voltage | V_{CEO} | $I_C = 1 \text{mA}, I_B = 0$ | 30 | | | |
| Emitter - base breakdown voltage | V_{EBO} | $I_E = 100 \mu\text{A}, I_C = 0$ | 5 | | | |
| Collector-base cut-off current | I_{CBO} | $V_{CB} = 50 \text{V}, I_E = 0$ | | | 0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = 5 \text{V}, I_C = 0$ | | | 0.1 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 10 \text{mA}, I_B = 1 \text{mA}$ | | | 0.3 | V |
| Base - emitter saturation voltage | $V_{BE(sat)}$ | $I_C = 10 \text{mA}, I_B = 1 \text{mA}$ | | | 1.2 | |
| Base - emitter voltage | V_{BE} | $V_{CE} = 6 \text{V}, I_C = 1 \text{mA}$ | 0.65 | | 0.75 | |
| DC current gain | h_{FE} | $V_{CE} = 6 \text{V}, I_C = 1 \text{mA}$ | 60 | | 180 | |
| Noise figure | NF | $V_{CE} = 6 \text{V}, I_E = -1 \text{mA}, f = 1 \text{MHz}, R_G = 500 \Omega$ | | | 4 | dB |
| Collector-base time constant | C_{C-rb} | $V_{CB} = 6 \text{V}, I_E = -10 \text{mA}, f = 31.9 \text{MHz}$ | | | 15 | ps |
| Collector output capacitance | C_{ob} | $V_{CB} = 6 \text{V}, I_E = 0, f = 1 \text{MHz}$ | | | 2.2 | pF |
| Transition frequency | f_T | $V_{CE} = 6 \text{V}, I_E = -1 \text{mA}$ | 150 | | | MHz |

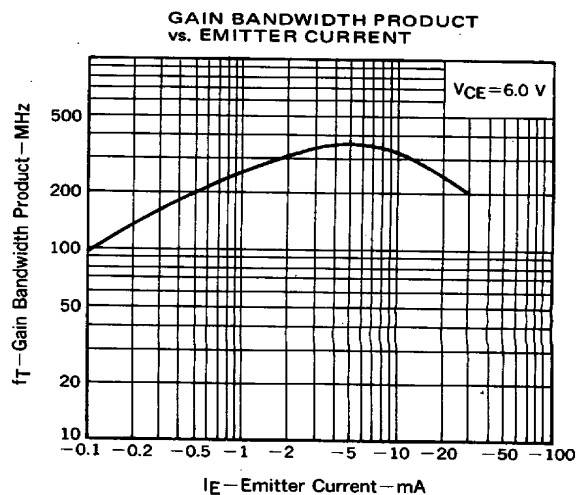
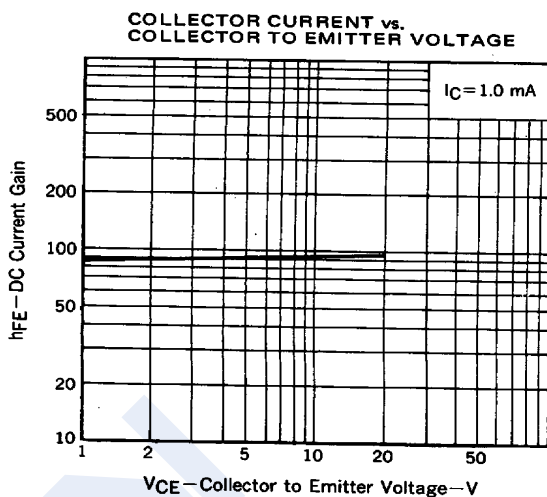
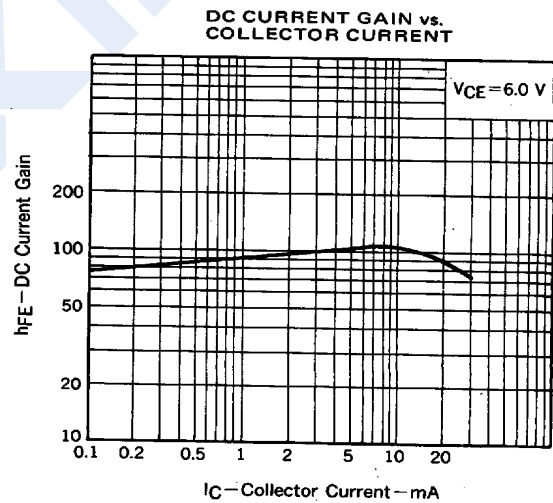
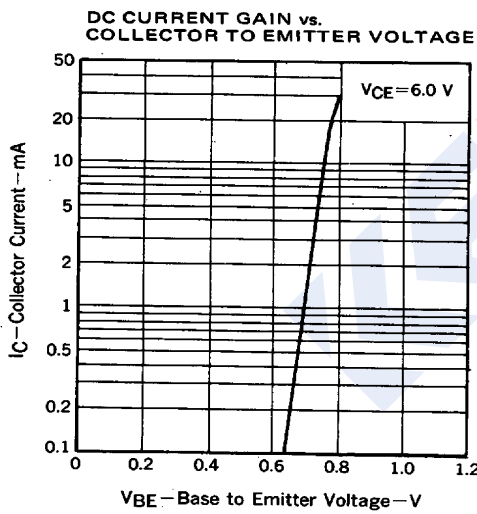
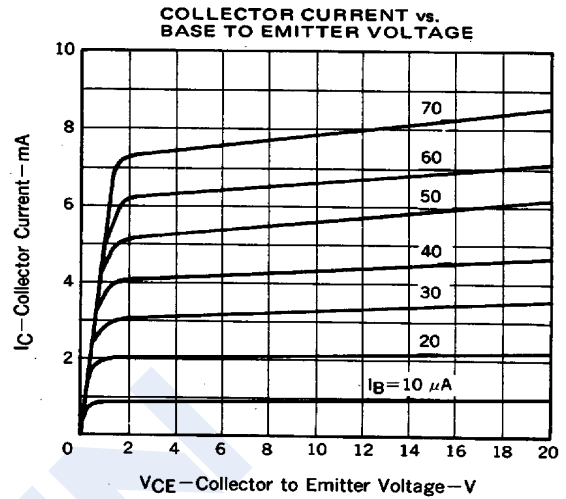
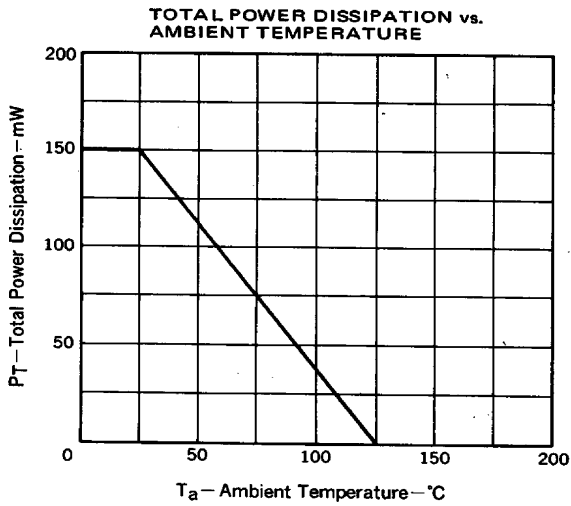
■ Classification of h_{FE}

| Type | 2SC1009-FA3 | 2SC1009-FA4 |
|---------|-------------|-------------|
| Range | 60-120 | 90-180 |
| Marking | FA3 | FA4 |

NPN Transistors

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■ Typical Characteristics

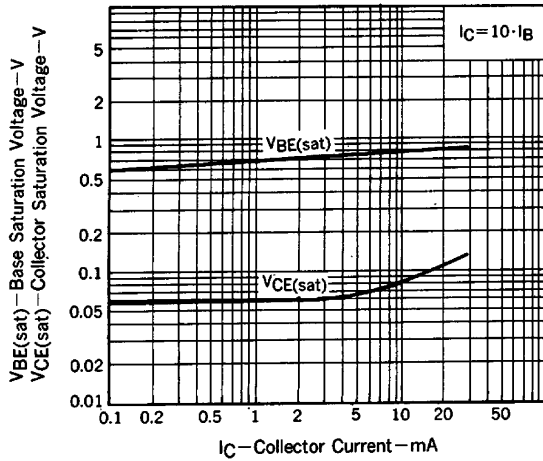


NPN Transistors

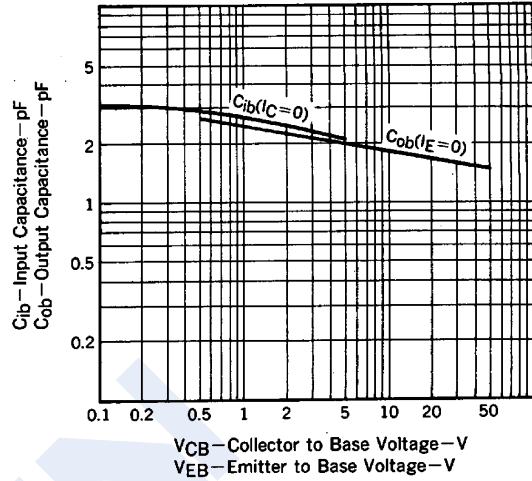
2SC1009

■ Typical Characteristics

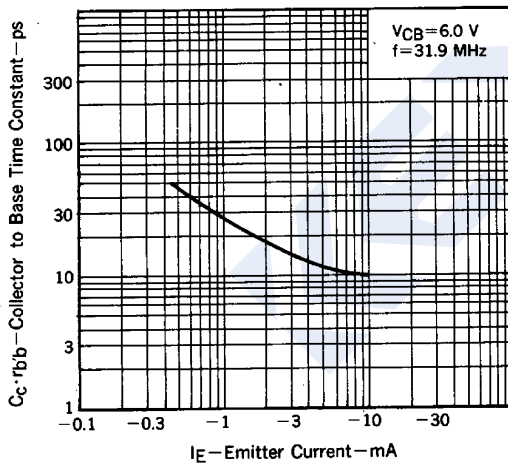
BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



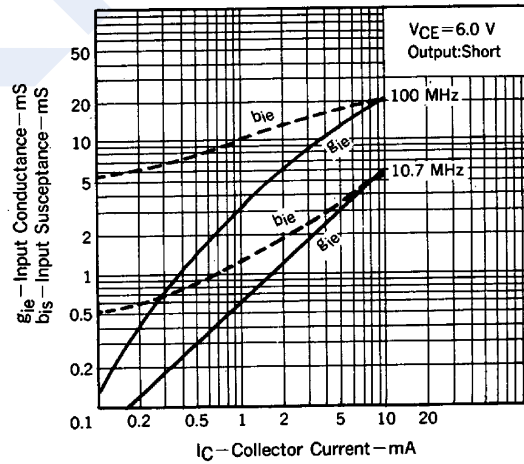
INPUT AND OUTPUT CAPACITANCE vs. REVERSE VOLTAGE



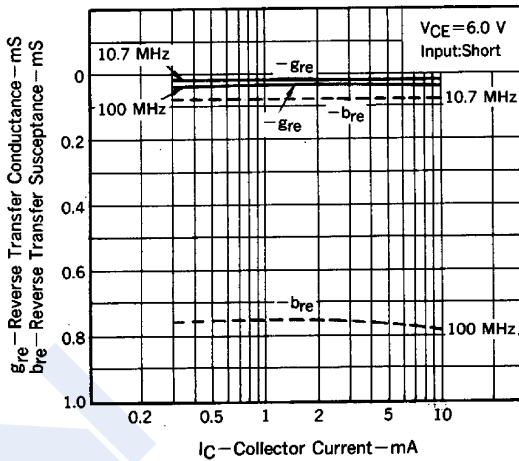
COLLECTOR TO BASE TIME CONSTANT vs. EMITTER CURRENT



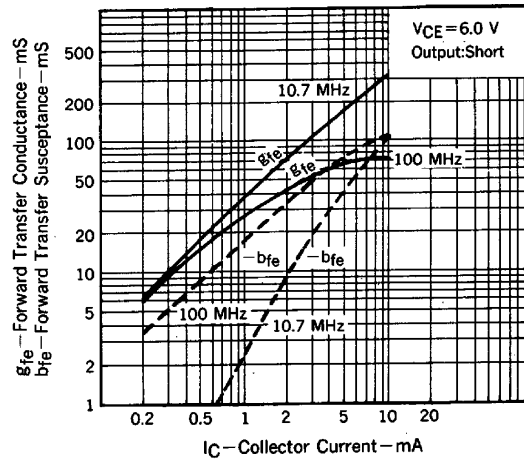
INPUT ADMITTANCE (y_{ie}) vs. COLLECTOR CURRENT



REVERSE TRANSFER ADMITTANCE (y_{re}) vs. COLLECTOR CURRENT



FORWARD TRANSFER ADMITTANCE (y_{fe}) vs. COLLECTOR CURRENT



NPN Transistors

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■ Typical Characteristics

